DUAL H-BRIDGE DRIVER IC

Check for Samples: DRV8841

FEATURES

- **Dual H-Bridge DC Motor Driver**
  - **Drives Two DC Motors, One Stepper Motor or Other Loads**
  - **Two-Bit Winding Current Control Allows Up to 4 Current Levels**
  - **Low MOSFET On-Resistance**
- **2.5-A Maximum Drive Current at 24 V, 25°C**
- **Built-In 3.3-V Reference Output**
- **Industry Standard Parallel Digital Control Interface**
- **8-V to 45-V Operating Supply Voltage Range**
- **Thermally Enhanced Surface Mount Package**

APPLICATIONS

- **Printers**
- **Scanners**
- **Office Automation Machines**
- **Gaming Machines**
- **Factory Automation**
- **Robotics**

DESCRIPTION

The DRV8841 provides an integrated motor driver solution for printers, scanners, and other automated equipment applications. The device has one H-bridge driver, and is intended to drive one DC motor. TThe device has two H-bridge drivers, and can be used to drive two DC motors, one stepper motor, or other loads. The output driver block for each consists of N-channel power MOSFET's configured as H-bridges. The DRV8841 can supply up to 2.5-A peak or 1.75-A RMS output current (with proper heatsinking at 24 V and 25°C) per H-bridge.

Separate inputs to independently control each half of the H-bridge are provided.

Internal shutdown functions are provided for over current protection, short circuit protection, under voltage lockout and overtemperature.

TheDRV8841 is available in a 28-pin HTSSOP package with PowerPAD™ (Eco-friendly: RoHS & no Sb/Br).

ORDERING INFORMATION(1)

T_A	PACKAGE(2)		ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	PowerPAD™ (HTSSOP) - PWP	Reel of 2000	DRV8841PWPR	8841

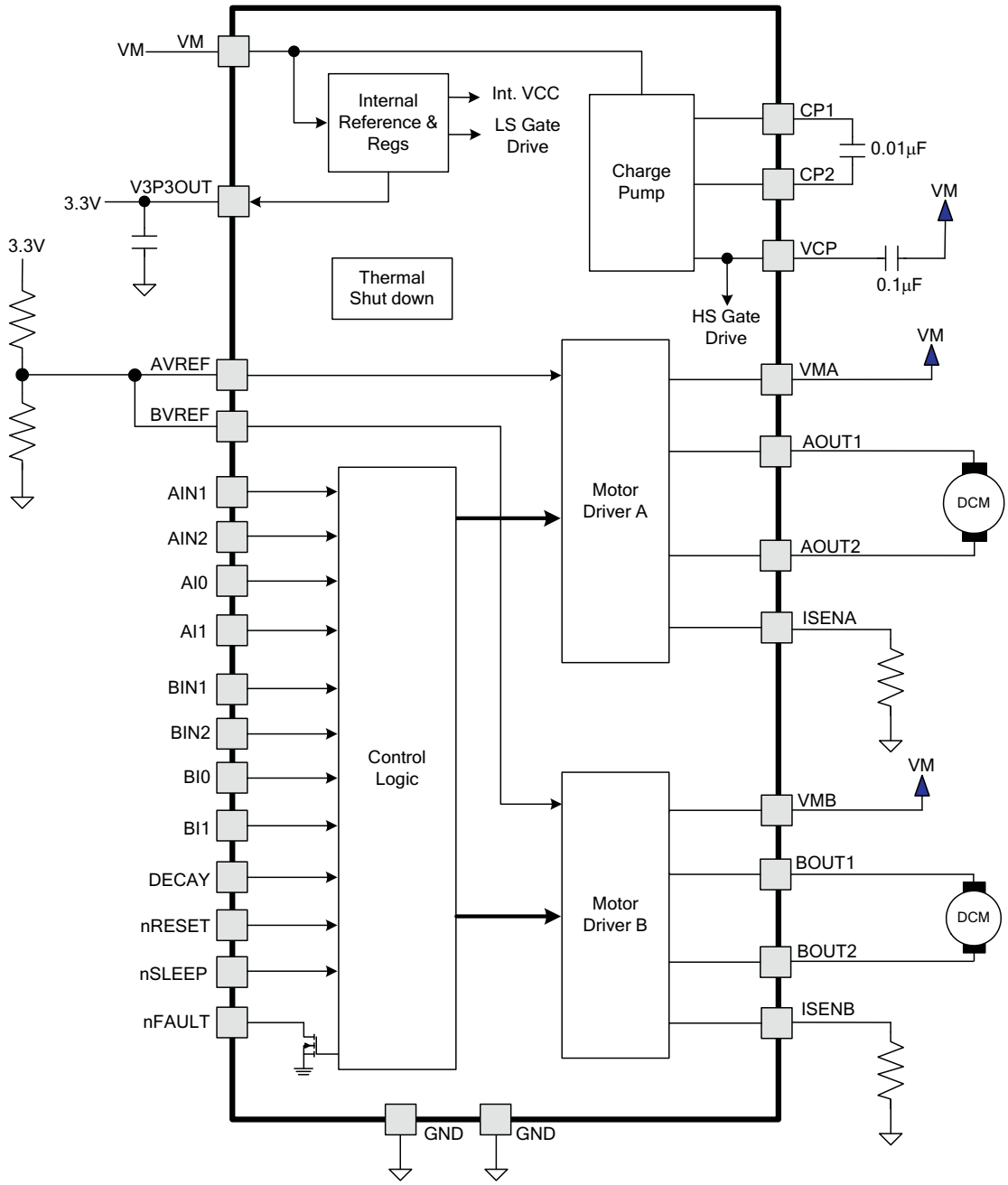
(1) For the most current packaging and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

PRODUCT PREVIEW

DEVICE INFORMATION

Functional Block Diagram



PRODUCT PREVIEW

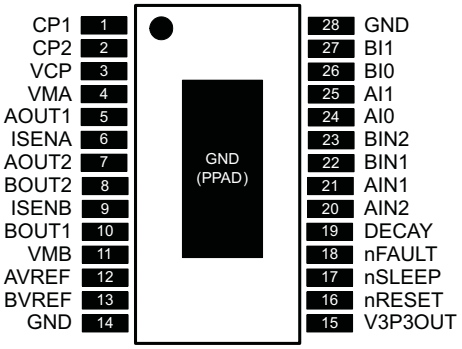
Table 1. TERMINAL FUNCTIONS

NAME	PIN	I/O(1)	DESCRIPTION	EXTERNAL COMPONENTS OR CONNECTIONS
POWER AND GROUND				
GND	14, 28	-	Device ground	
VMA	4	-	Bridge A power supply	Connect to motor supply (8 - 45 V). Both pins must be connected to same supply.
VMB	11	-	Bridge B power supply	
V3P3OUT	15	O	3.3-V regulator output	Bypass to GND with a 0.47-μF 6.3-V ceramic capacitor. Can be used to supply VREF.
CP1	1	IO	Charge pump flying capacitor	Connect a 0.01-μF 50-V capacitor between CP1 and CP2.
CP2	2	IO	Charge pump flying capacitor	
VCP	3	IO	High-side gate drive voltage	Connect a 0.1-μF 16-V ceramic capacitor to VM.
CONTROL				
AIN1	21	I	Bridge A input 1	Logic input controls state of AOUT1
AIN2	20	I	Bridge A input 2	Logic input controls state of AOUT2
AI0	24	I	Bridge A current set	Sets bridge A current: 00 = 100%, 01 = 71%, 10 = 38%, 11 = 0
AI1	25	I		
BIN1	22	I	Bridge B input 1	Logic input controls state of BOUT1
BIN2	23	I	Bridge B input 2	Logic input controls state of BOUT2
BI0	26	I	Bridge B current set	Sets bridge B current: 00 = 100%, 01 = 71%, 10 = 38%, 11 = 0
BI1	27	I		
DECAY	19	I	Decay mode	Low = slow decay, open = mixed decay, high = fast decay
nRESET	16	I	Reset input	Active-low reset input initializes internal logic and disables the H-bridge outputs
nSLEEP	17	I	Sleep mode input	Logic high to enable device, logic low to enter low-power sleep mode
AVREF	12	I	Bridge A current set reference input	Reference voltage for winding current set. Can be driven individually with an external DAC for microstepping, or tied to a reference (e.g., V3P3OUT).
BVREF	13	I	Bridge B current set reference input	
STATUS				
nFAULT	18	OD	Fault	Logic low when in fault condition (overtemp, overcurrent)
OUTPUT				
ISENA	6	IO	Bridge A ground / Isense	Connect to current sense resistor for bridge A
ISENB	9	IO	Bridge B ground / Isense	Connect to current sense resistor for bridge B
AOUT1	5	O	Bridge A output 1	Connect to motor winding A
AOUT2	7	O	Bridge A output 2	
BOUT1	10	O	Bridge B output 1	Connect to motor winding B
BOUT2	8	O	Bridge B output 2	

(1) Directions: I = input, O = output, OZ = tri-state output, OD = open-drain output, IO = input/output

PRODUCT PREVIEW

PWP PACKAGE
(TOP VIEW)



ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) (1) (2)

		VALUE	UNIT
VMx	Power supply voltage range	–0.3 to 47	V
	Digital pin voltage range	–0.5 to 7	V
VREF	Input voltage	–0.3 to 4	V
	ISENSEx pin voltage	–0.3 to 0.8	V
	Peak motor drive output current, t < 1 μS	Internally limited	A
	Continuous motor drive output current(3)	2.5	A
	Continuous total power dissipation	See Dissipation Ratings table	
T_J	Operating virtual junction temperature range	–40 to 150	°C
T_A	Operating ambient temperature range	–40 to 85	°C
T_{stg}	Storage temperature range	–60 to 150	°C

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute–maximum–rated conditions for extended periods may affect device reliability.
(2) All voltage values are with respect to network ground terminal.
(3) Power dissipation and thermal limits must be observed.

DISSIPATION RATINGS (PRELIMINARY)

BOARD	PACKAGE	$R_{\theta JA}$	DERATING FACTOR ABOVE T_A = 25°C	T_A < 25°C	T_A = 70°C	T_A = 85°C
Low-K(1)	PWP	67.5°C/W	14.8 mW/°C	1.85 W	1.18 W	0.96 W
Low-K(2)		39.5°C/W	25.3 mW/°C	3.16 W	2.02 W	1.64 W
High-K(3)		33.5°C/W	29.8 mW/°C	3.73 W	2.38 W	1.94 W
High-K(4)		28°C/W	35.7 mW/°C	4.46 W	2.85 W	2.32 W

(1) The JEDEC Low-K board used to derive this data was a 76-mm x 114-mm, 2-layer, 1.6-mm thick PCB with no backside copper.
(2) The JEDEC Low-K board used to derive this data was a 76-mm x 114-mm, 2-layer, 1.6-mm thick PCB with 25-cm^2 2-oz copper on back side.
(3) The JEDEC High-K board used to derive this data was a 76-mm x 114-mm, 4-layer, 1.6-mm thick PCB with no backside copper and solid 1-oz internal ground plane.
(4) The JEDEC High-K board used to derive this data was a 76-mm x 114-mm, 4-layer, 1.6-mm thick PCB with 25-cm^2 1-oz copper on back side and solid 1-oz internal ground plane.

PRODUCT PREVIEW

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_M	Motor power supply voltage range(1)	8		45	V
V_{REF}	VREF input voltage(2)	1		3.5	V
I_{V3P3}	V3P3OUT load current			1	mA

(1) All V_M pins must be connected to the same supply voltage.
(2) Operational at VREF between 0 V and 1 V, but accuracy is degraded.

ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER SUPPLIES						
I_{VM}	VM operating supply current	V_M = 24 V, f_{PWM} < 50 kHz		5	8	mA
I_{VMQ}	VM sleep mode supply current	V_M = 24 V		10	20	µA
V_{UVLO}	VM undervoltage lockout voltage	V_M rising		9	10	V
V3P3OUT REGULATOR						
V_{3P3}	V3P3OUT voltage	IOUT = 0 to 1 mA	3.2	3.3	3.4	V
LOGIC-LEVEL INPUTS						
V_{IL}	Input low voltage			0.6	0.7	V
V_{IH}	Input high voltage		2		5.25	V
V_{HYS}	Input hysteresis		0.3	0.45	0.6	V
I_{IL}	Input low current	VIN = 0	–20		20	µA
I_{IH}	Input high current	VIN = 3.3 V			100	µA
nFAULT OUTPUT (OPEN-DRAIN OUTPUT)						
V_{OL}	Output low voltage	I_O = 5 mA			0.5	V
I_{OH}	Output high leakage current	V_O = 3.3 V			1	µA
DECAY INPUT						
V_{IL}	Input low threshold voltage	For slow decay (brake) mode	0		0.8	V
V_{IH}	Input high threshold voltage	For fast decay (coast) mode	2			V
I_{IN}	Input current	VIN = 0 V to 3.3 V	–25		25	µA
H-BRIDGE FETS						
$R_{DS(ON)}$	HS FET on resistance	V_M = 24 V, I_O = 1 A, T_J = 25°C		TBD		Ω
		V_M = 24 V, I_O = 1 A, T_J = 85°C		0.30	TBD	
$R_{DS(ON)}$	LS FET on resistance	V_M = 24 V, I_O = 1 A, T_J = 25°C		TBD		Ω
		V_M = 24 V, I_O = 1 A, T_J = 85°C		0.30	TBD	
I_{OFF}	Off-state leakage current		–20		20	µA
MOTOR DRIVER						
f_{PWM}	PWM frequency		45	50	55	kHz
t_{BLANK}	Current sense blanking time			3.75		µs
t_R	Rise time		50		300	ns
t_F	Fall time		50		300	ns
PROTECTION CIRCUITS						
I_{OCP}	Overcurrent protection trip level		TBD		TBD	A
t_{TSD}	Thermal shutdown temperature	Die temperature	150	160	180	°C

PRODUCT PREVIEW

ELECTRICAL CHARACTERISTICS (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
CURRENT CONTROL						
I_{REF}	VREF input current	VREF = 3.3 V	–3		3	μA
V_{TRIP}	xISENSE trip voltage	xVREF = 3.3 V, 100% current setting	635	660	685	mV
		xVREF = 3.3 V, 71% current setting	445	469	492	
		xVREF = 3.3 V, 38% current setting	225	251	276	
A_{ISENSE}	Current sense amplifier gain	Reference only		5		V/V

PRODUCT PREVIEW

FUNCTIONAL DESCRIPTION

PWM Motor Drivers

The DRV8841 contains two H-bridge motor drivers with current-control PWM circuitry. A block diagram of the motor control circuitry is shown in Figure 1.

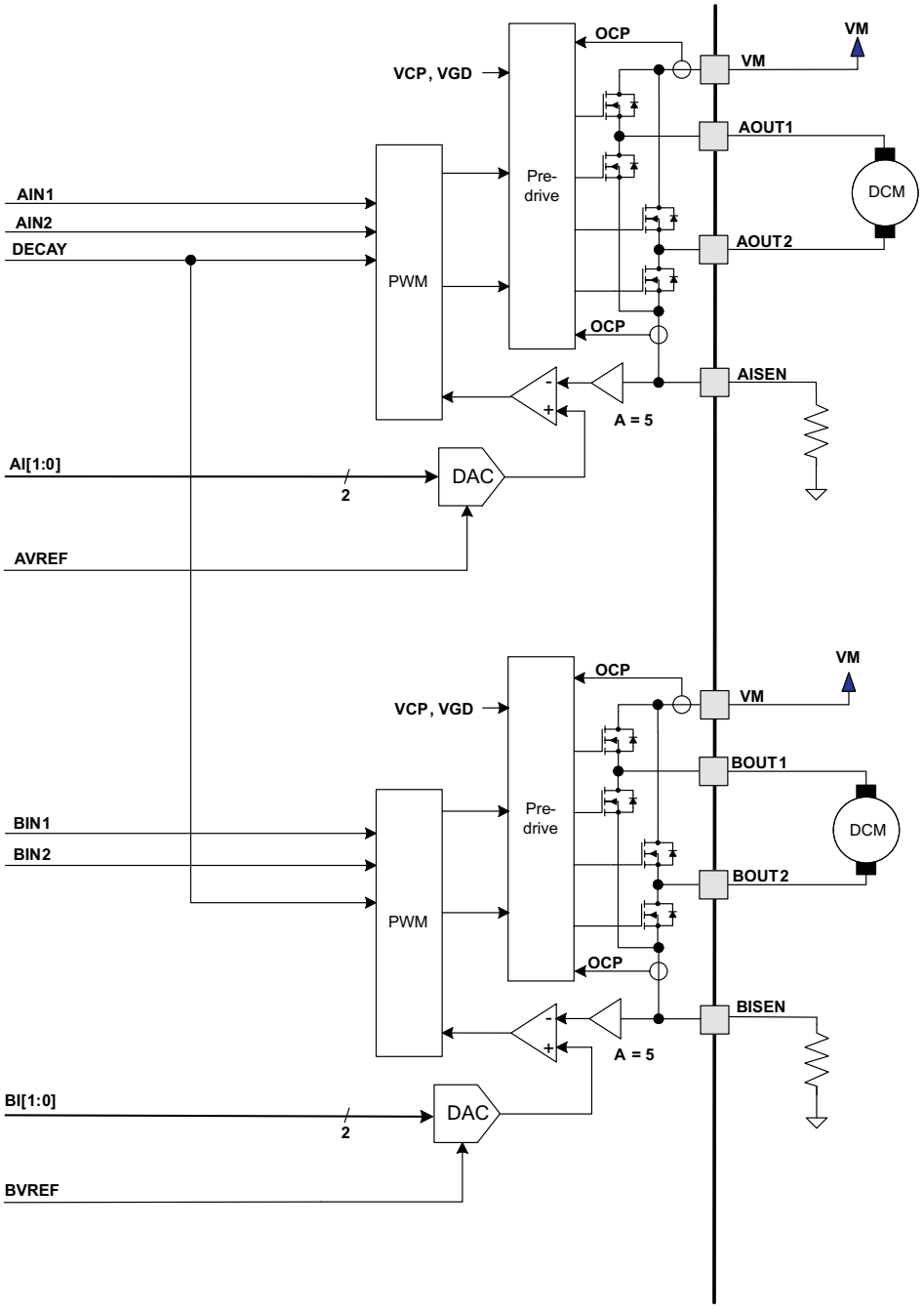


Figure 1. Motor Control Circuitry

Note that there are multiple VM pins. All VM pins must be connected together to the motor supply voltage.

Bridge Control

The AIN1 and AIN2 input pins directly control the state of the AOUT1 and AOUT2 outputs; similarly, the BIN1 and BIN2 input pins directly control the state of the BOUT1 and BOUT2 outputs. Either input can also be used for PWM control of the load. Table 2 shows the logic.

Table 2. H-Bridge Logic

xIN1	xIN2	xOUT1	xOUT2
0	0	L	L
0	1	L	H
1	0	H	L
1	1	H	H

Current Regulation

The current through the motor windings is regulated by a fixed-frequency PWM current regulation, or current chopping. When an H-bridge is enabled, current rises through the winding at a rate dependent on the DC voltage and inductance of the winding. Once the current hits the current chopping threshold, the bridge disables the current until the beginning of the next PWM cycle.

For stepping motors, current regulation is normally used at all times, and can changing the current can be used to microstep the motor. For DC motors, current regulation is used to limit the start-up and stall current of the motor.

The PWM chopping current is set by a comparator which compares the voltage across a current sense resistor connected to the xISEN pins, multiplied by a factor of 5, with a reference voltage. The reference voltage is input from the xVREF pins, and is scaled by a 2-bit DAC that allows current settings of 100%, 71%, 38% of full-scale, plus zero.

The full-scale (100%) chopping current is calculated in Equation 1.

$$I_{CHOP} = \frac{V_{REFX}}{5 \bullet R_{ISENSE}} \quad (1)$$

Example:

If a 0.25-Ω sense resistor is used and the VREFx pin is 2.5 V, the full-scale (100%) chopping current will be 2.5 V / (5 x 0.25 Ω) = 2 A.

Two input pins per H-bridge (xI1 and xI0) are used to scale the current in each bridge as a percentage of the full-scale current set by the VREF input pin and sense resistance. The function of the pins is shown in Table 3.

Table 3. H-Bridge Pin Functions

xI1	xI0	RELATIVE CURRENT (% FULL-SCALE CHOPPING CURRENT)
1	1	0% (Bridge disabled)
1	0	38%
0	1	71%
0	0	100%

Note that when both xI bits are 1, the H-bridge is disabled and no current flows.

Example:

If a 0.25-Ω sense resistor is used and the VREF pin is 2.5 V, the chopping current will be 2 A at the 100% setting (xI1, xI0 = 00). At the 71% setting (xI1, xI0 = 01) the current will be 2 A x 0.71 = 1.42 A, and at the 38% setting (xI1, xI0 = 10) the current will be 2 A x 0.38 = 0.76 A. If (xI1, xI0 = 11) the bridge will be disabled and no current will flow.

Decay Mode

During PWM current chopping, the H-bridge is enabled to drive current through the motor winding until the PWM current chopping threshold is reached. This is shown in Figure 2 as case 1. The current flow direction shown indicates the state when the xIN1 pin is high and the xIN2 pin is low.

Once the chopping current threshold is reached, the H-bridge can operate in two different states, fast decay or slow decay.

In fast decay mode, once the PWM chopping current level has been reached, the H-bridge reverses state to allow winding current to flow in a reverse direction. As the winding current approaches zero, the bridge is disabled to prevent any reverse current flow. Fast decay mode is shown in Figure 2 as case 2.

In slow decay mode, winding current is re-circulated by enabling both of the low-side FETs in the bridge. This is shown in Figure 2 as case 3.

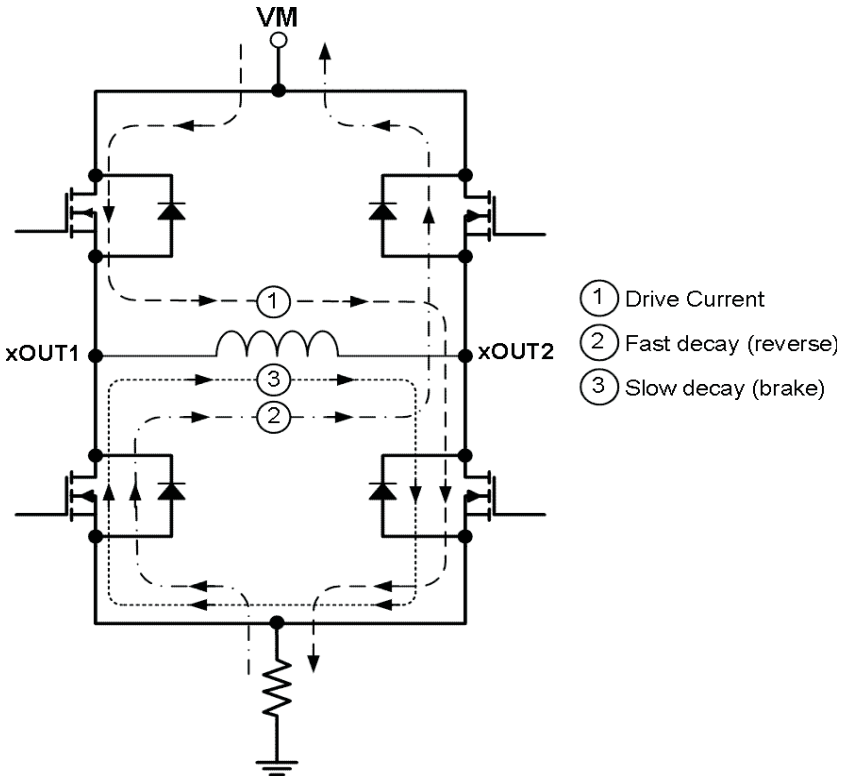


Figure 2. Decay Mode

The DRV8841 supports fast decay, slow decay and a mixed decay mode. Slow, fast, or mixed decay mode is selected by the state of the DECAY pin - logic low selects slow decay, open selects mixed decay operation, and logic high sets fast decay mode. Note that the DECAY pin sets the decay mode for both H-bridges.

Mixed decay mode begins as fast decay, but at a fixed period of time (75% of the PWM cycle) switches to slow decay mode for the remainder of the fixed PWM period.

Blanking Time

After the current is enabled in an H-bridge, the voltage on the xISEN pin is ignored for a fixed period of time before enabling the current sense circuitry. This blanking time is fixed at 3.75 μs. Note that the blanking time also sets the minimum on time of the PWM.

nRESET and nSLEEP Operation

The nRESET pin, when driven active low, resets the internal logic. It also disables the H-bridge drivers. All inputs are ignored while nRESET is active.

Driving nSLEEP low will put the device into a low power sleep state. In this state, the H-bridges are disabled, the gate drive charge pump is stopped, the V3P3OUT regulator is disabled, and all internal clocks are stopped. In this state all inputs are ignored until nSLEEP returns inactive high. When returning from sleep mode, some time (approximately 1 ms) needs to pass before the motor driver becomes fully operational.

Protection Circuits

The DRV8841 is fully protected against undervoltage, overcurrent and overtemperature events.

Overcurrent Protection (OCP)

An analog current limit circuit on each FET limits the current through the FET by removing the gate drive. If this analog current limit persists for longer than the OCP time, all FETs in the H-bridge will be disabled and the nFAULT pin will be driven low. The device will remain disabled until either nRESET pin is applied, or VM is removed and re-applied.

Overcurrent conditions on both high and low side devices; i.e., a short to ground, supply, or across the motor winding will all result in an overcurrent shutdown. Note that overcurrent protection does not use the current sense circuitry used for PWM current control, and is independent of the I_{SENSE} resistor value or VREF voltage.

Thermal Shutdown (TSD)

If the die temperature exceeds safe limits, all FETs in the H-bridge will be disabled and the nFAULT pin will be driven low. Once the die temperature has fallen to a safe level operation will automatically resume.

Undervoltage Lockout (UVLO)

If at any time the voltage on the VM pins falls below the undervoltage lockout threshold voltage, all circuitry in the device will be disabled and internal logic will be reset. Operation will resume when V_M rises above the UVLO threshold.

THERMAL INFORMATION

Thermal Protection

The DRV8841 has thermal shutdown (TSD) as described above. If the die temperature exceeds approximately 150°C, the device will be disabled until the temperature drops to a safe level.

Any tendency of the device to enter TSD is an indication of either excessive power dissipation, insufficient heatsinking, or too high an ambient temperature.

Power Dissipation

Power dissipation in the DRV8841 is dominated by the power dissipated in the output FET resistance, or RDS(ON). Average power dissipation of each H-bridge when running a DC motor can be roughly estimated by Equation 2.

$$P = 2 \bullet R_{DS(ON)} \bullet (I_{OUT})^2 \quad (2)$$

where P is the power dissipation of one H-bridge, $R_{DS(ON)}$ is the resistance of each FET, and I_{OUT} is the RMS output current being applied to each winding. I_{OUT} is equal to the average current drawn by the DC motor. Note that at start-up and fault conditions this current is much higher than normal running current; these peak currents and their duration also need to be taken into consideration. The factor of 2 comes from the fact that at any instant two FETs are conducting winding current (one high-side and one low-side).

The total device dissipation will be the power dissipated in each of the two H-bridges added together.

The maximum amount of power that can be dissipated in the device is dependent on ambient temperature and heatsinking.

Note that $R_{DS(ON)}$ increases with temperature, so as the device heats, the power dissipation increases. This must be taken into consideration when sizing the heatsink.

Heatsinking

The PowerPAD™ package uses an exposed pad to remove heat from the device. For proper operation, this pad must be thermally connected to copper on the PCB to dissipate heat. On a multi-layer PCB with a ground plane, this can be accomplished by adding a number of vias to connect the thermal pad to the ground plane. On PCBs without internal planes, copper area can be added on either side of the PCB to dissipate heat. If the copper area is on the opposite side of the PCB from the device, thermal vias are used to transfer the heat between top and bottom layers.

For details about how to design the PCB, refer to TI application report SLMA002, " PowerPAD™ Thermally Enhanced Package" and TI application brief SLMA004, " PowerPAD™ Made Easy", available at www.ti.com.

In general, the more copper area that can be provided, the more power can be dissipated.

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